MOSFETs Silicon N-Channel MOS

SSM3K2615TU

1. Applications

- Load Switches
- Motor Drivers

2. Features

(1) 3.3-V gate drive voltage.

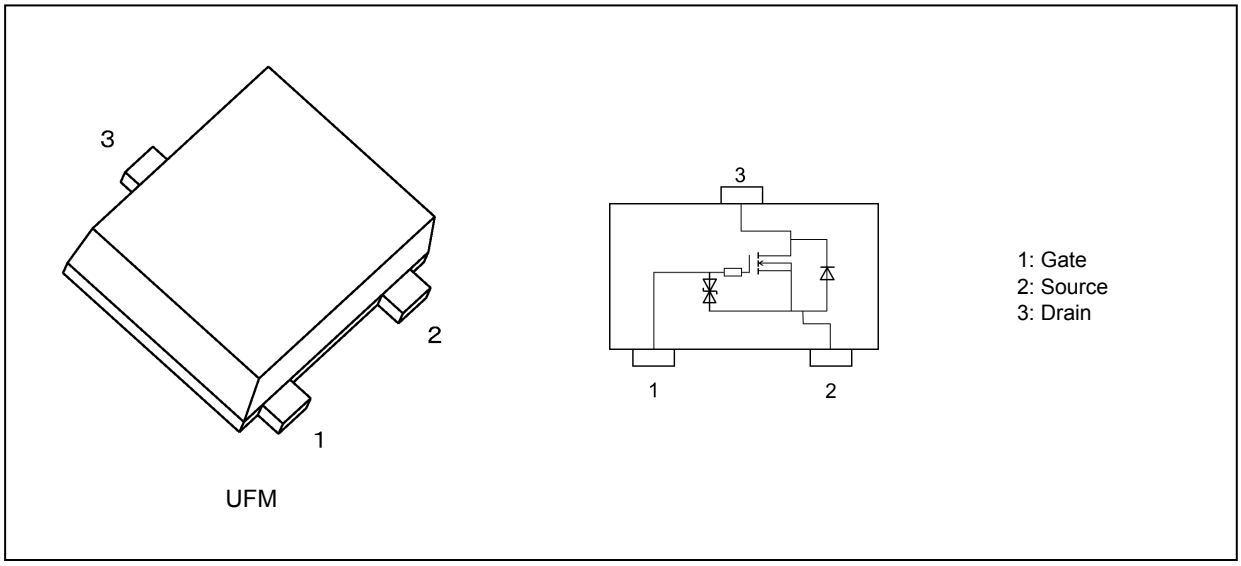
(2) Low drain-source on-resistance

: $R_{DS(ON)}$ = 380 mΩ (typ.) (@V_{GS} = 3.3 V, I_D = 0.5 A)

$R_{DS(ON)}$ = 330 mΩ (typ.) (@V_{GS} = 4.0 V, I_D = 1.0 A)

$R_{DS(ON)}$ = 230 mΩ (typ.) (@V_{GS} = 10 V, I_D = 1.0 A)

3. Packaging and Pin Assignment



Start of commercial production

2016-06

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4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	60	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)		(Note 1)	I_D	2	A
Drain current (pulsed)		(Note 1), (Note 2)	I_{DP}	6	
Power dissipation		(Note 3)	P_D	0.8	W
Power dissipation	(t = 10 s)	(Note 3)	P_D	1.6	
Channel temperature			T_{ch}	150	°C
Single-pulse avalanche energy		(Note 4)	E_{AS}	52.9	mJ
Avalanche current			I_{AR}	2	A
Storage temperature			T_{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Pulse width (PW) ≤ 10 ms, duty ≤ 1%

Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm^2)

Note 4: V_{DD} = 25 V, T_{ch} = 25°C (Initial state), L = 20 mH, R_G = 25Ω, I_{AR} = 2A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

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5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{DS} = 0 V, V_{GS} = ±16 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V	—	—	1	
Drain-source breakdown voltage		$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	60	—	—	V
Gate threshold voltage	(Note 1)	V_{th}	V_{DS} = 10 V, I_D = 1 mA	0.8	—	2.0	V
Drain-source on-resistance	(Note 2)	$R_{DS(ON)}$	I_D = 0.5 A, V_{GS} = 3.3 V	—	0.38	0.58	Ω
			I_D = 1.0 A, V_{GS} = 4.0 V	—	0.33	0.44	
			I_D = 1.0 A, V_{GS} = 10 V	—	0.23	0.30	
Forward transfer admittance	(Note 2)	$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 1.0 A	1.0	2.0	—	S

Note 1: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th}, and $V_{GS(OFF)}$ must be lower than V_{th}. This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.
Take this into consideration when using the device.

Note 2: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	150	—	pF
Reverse transfer capacitance	C_{rss}		—	25	—	
Output capacitance	C_{oss}		—	70	—	
Switching time (rise time)	t_r	V_{DD} ≈ 30 V, I_D = 1 A, V_{GS} = 0 to 10 V, R_G = 50 Ω	—	25	—	ns
Switching time (turn-on time)	t_{on}		—	30	—	
Switching time (fall time)	t_f		—	50	—	
Switching time (turn-off time)	t_{off}		—	150	—	

5.3. Switching Time Test Circuit

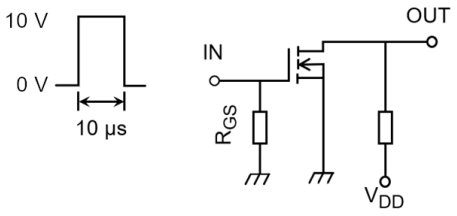


Fig. 5.3.1 Switching Time Test Circuit

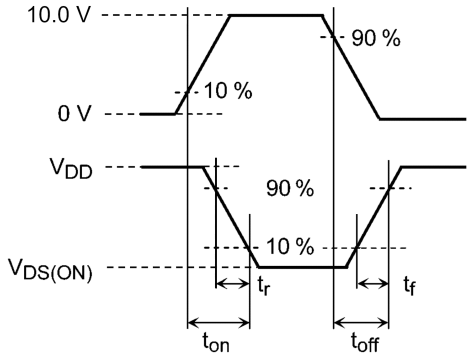


Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 48 V, V_{GS} = 10 V, I_D = 2.0 A	—	6.0	—	nC
Gate-source charge 1	Q_{gs1}		—	0.5	—	
Gate-drain charge	Q_{gd}		—	1.4	—	

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5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC)	(Note 1)	I_{DR}	—	—	—	2	A
Reverse drain current (pulsed)	(Note 1)	I_{DRP}	—	—	—	6	A
Diode forward voltage	(Note 2)	V_{DSF}	I_D = -2.0 A, V_{GS} = 0 V	—	-0.9	-1.5	V
Reverse recovery time		t_{rr}	I_{DR} = 2 A, V_{GS} = 0 V, dI_{DR}/dt = 50 A/μs	—	100	—	ns
Reverse recovery charge		Q_{rr}		—	40	—	nC

Note 1: Ensure that the channel temperature does not exceed 150 °C.
Note 2: Pulse measurement.

6. Marking

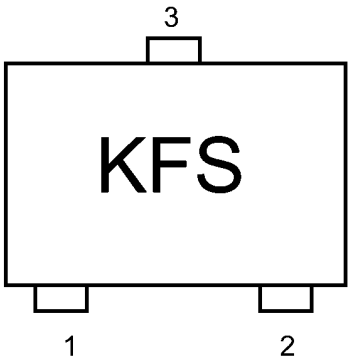


Fig. 6.1 Marking

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7. Characteristics Curves (Note)

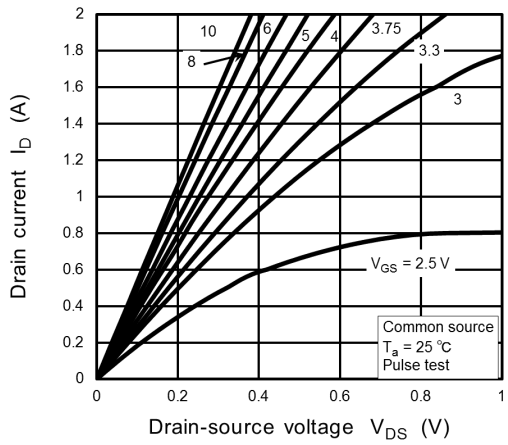


Fig. 7.1 I_D - V_{DS}

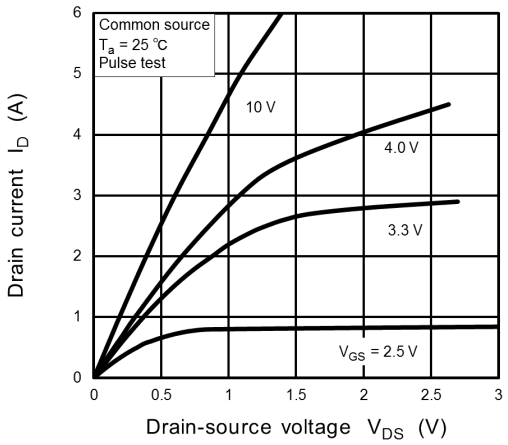


Fig. 7.2 I_D - V_{DS}

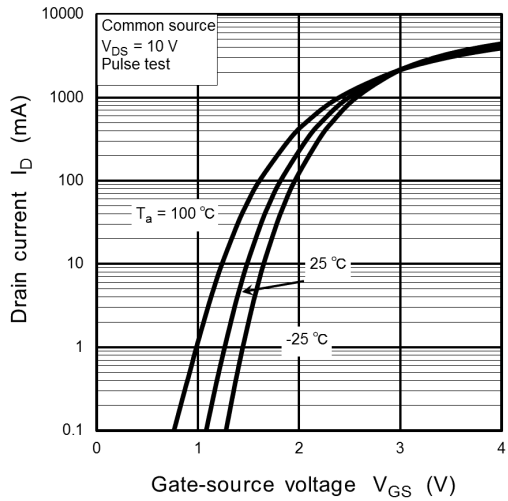


Fig. 7.3 I_D - V_{GS}

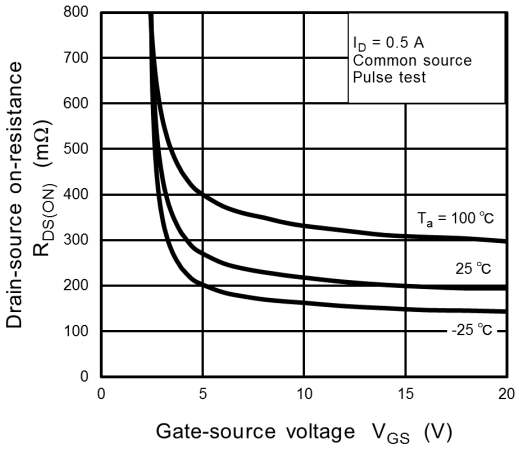


Fig. 7.4 $R_{DS(ON)}$ - V_{GS}

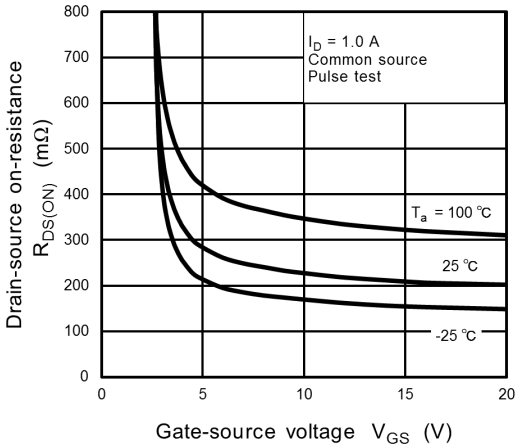


Fig. 7.5 $R_{DS(ON)}$ - V_{GS}

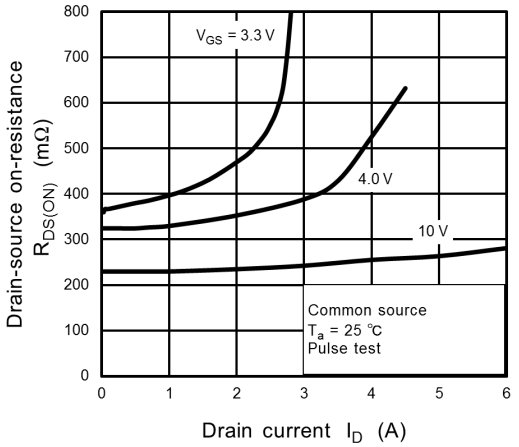


Fig. 7.6 $R_{DS(ON)}$ - I_D

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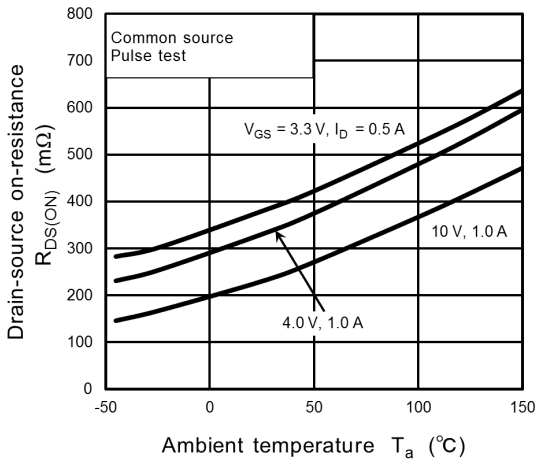


Fig. 7.7 $R_{DS(ON)}$ - T_a

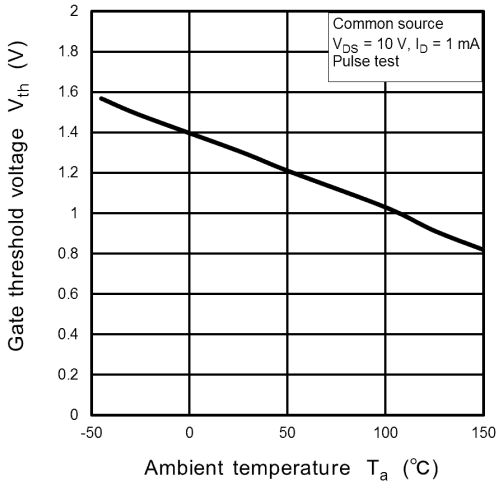


Fig. 7.8 V_{th} - T_a

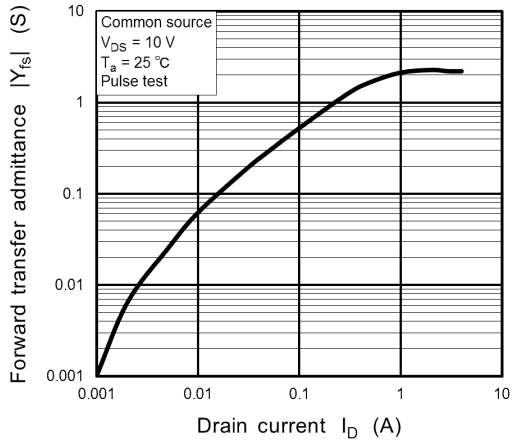


Fig. 7.9 $|Y_{fs}|$ - I_D

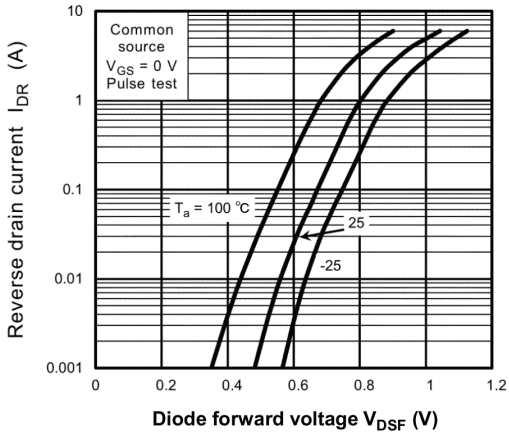


Fig. 7.10 I_{DR} - V_{DSF}

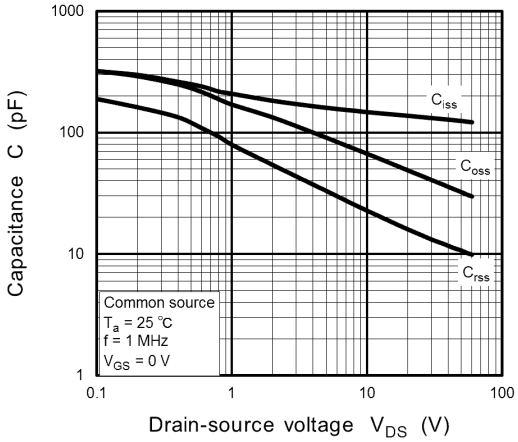


Fig. 7.11 C - V_{DS}

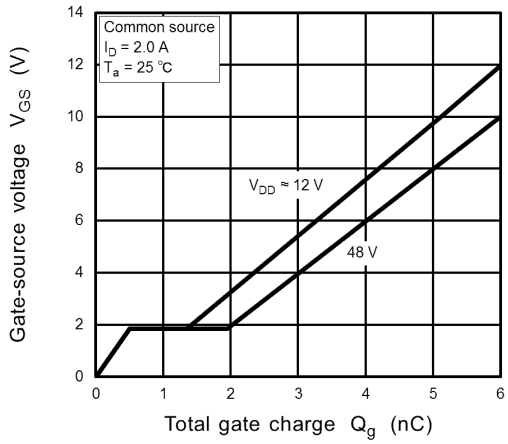


Fig. 7.12 Dynamic Input Characteristics

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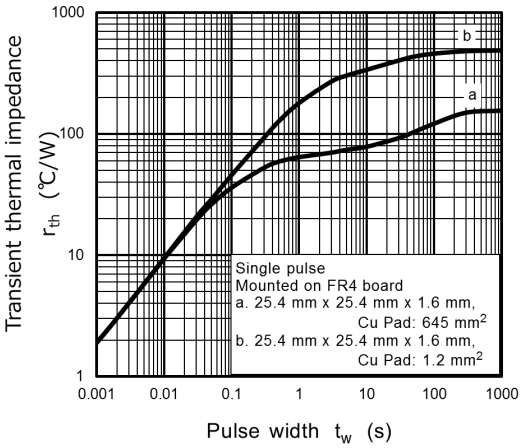


Fig. 7.13 r_{th} - t_w

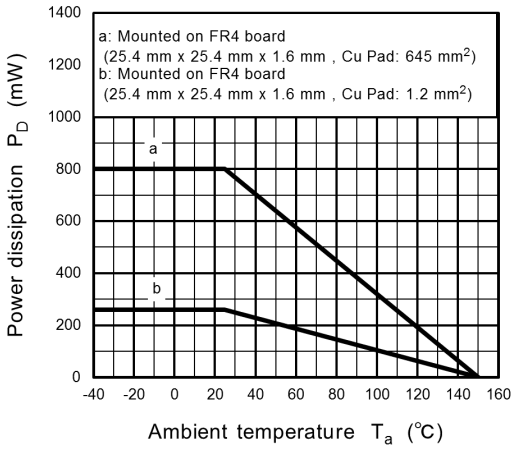


Fig. 7.14 P_D - T_a

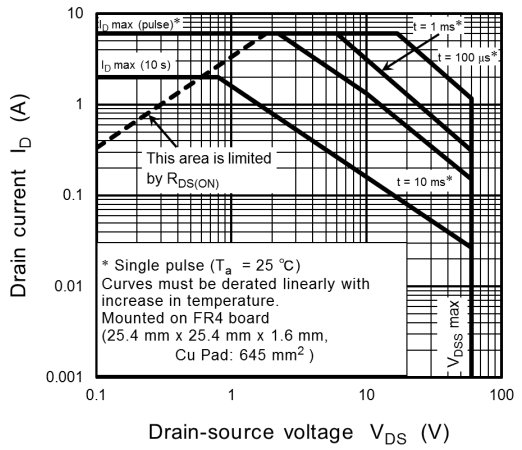


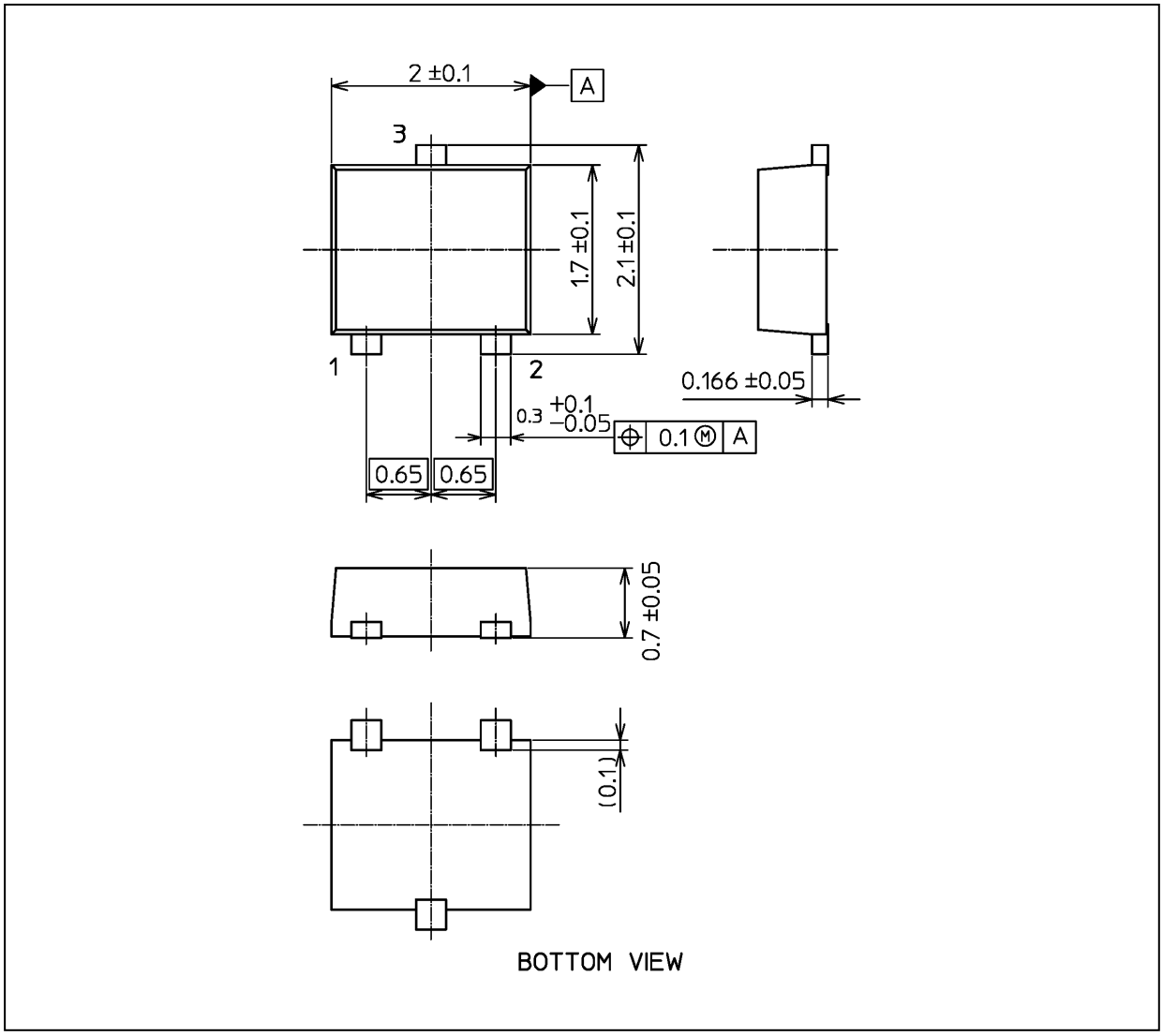
Fig. 7.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 6.6 mg (typ.)

Package Name(s)
Nickname: UFM

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